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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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MPSA₁₂

NPN Darlington Transistor

- This device is designed for applications requiring extremely high current gain at currents to 1.0A.
- Sourced from process 05.
- · See MPSA14 for characteristics.



1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings * T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	20	V
V _{CBO}	Collector-Base Voltage	20	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current - Continuous	1.2	Α
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 ~ +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Chara	Off Characteristics					
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \mu A, I_{E} = 0$	20			V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 15V, I_{E} = 0$			100	nA
I _{CES}	Emitter Cutoff Current	$V_{CB} = 15V, I_{C} = 0$			100	nA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 10V, I_{C} = 0$			100	nA
On Characteristics *						
h _{FE}	DC Current Gain	$V_{CE} = 5.0V, I_{C} = 10mA$	20,000			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 10mA, I_B = 0.01mA$			1.0	V
V _{BE} (on)	Base-Emitter On Voltage	$I_C = 10 \text{mA}, V_{CE} = 5.0 \text{V}$			1.4	V

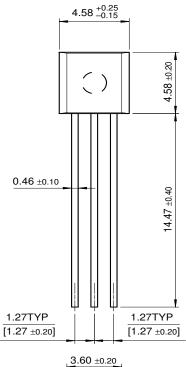
^{*} Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2.0%

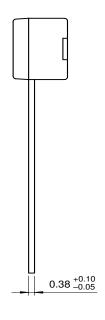
Thermal Characteristics $T_A=25$ °C unless otherwise noted

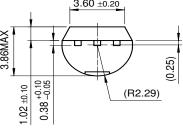
Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

Package Dimensions

TO-92







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Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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